

L Number	Hits	Search Text	DB	Time stamp
1	10717	257/68,71,295-314,324-326;438/3,240.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:40
2	189	257/68,71,295-314,324-326;438/3,240.ccls. and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:10
3	98	(257/68,71,295-314,324-326;438/3,240.ccls. and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3))) and ((wir\$3 bit) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:06
4	1	"6515573".PN.	USPAT	2004/02/06 12:15
5	1	"6351410".PN.	USPAT	2004/02/06 12:18
6	2	("6379978" "6473336").PN.	USPAT	2004/02/06 12:19
7	20	("5304975" "5365212" "5500633" "5523172" "5534355" "5578385" "5616370" "5700588" "5716719" "5734605" "5745406" "5747859" "5773156" "5825685" "5930164" "5973334" "6021065" "6069820" "6111783" "6114056").PN.	USPAT	2004/02/06 12:29
8	1	("6211005" "2001/0035545").PN.	USPAT	2004/02/06 12:54
9	12	("5281485" "5341118" "5608593" "5640343" "5801984" "5841692" "5898547" "6097625" "6153320" "6174582" "6295186" "6297983").PN.	USPAT	2004/02/06 12:56
10	103	(257/68,71,295-314,324-326;438/3,240.ccls. and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3))) and ((wir\$3 bit write) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:15
11	162	257/68,71,295-314,324-326;438/3,240.ccls. and (magnetic NEAR memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:14
12	152	(257/68,71,295-314,324-326;438/3,240.ccls. and (magnetic NEAR memory)) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:38
13	86	((257/68,71,295-314,324-326;438/3,240.ccls. and (magnetic NEAR memory)) and substrate) and transistor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:09
14	49	((((257/68,71,295-314,324-326;438/3,240.ccls. and (magnetic NEAR memory)) and substrate) and transistor\$1) and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:15
15	388805	257/\$.ccls. 438/\$.ccls. 365/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:14
16	2033	(257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (magnetic NEAR memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:14

17	299	((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:15
18	151	((((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)) and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:38
19	134	(((((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)) and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3)))) and ((wir\$3 bit write) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:39
20	0	(257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (((wir\$3 write) NEAR (line\$1 lead\$1)) WITH (width length) WITH (greater longer) WITH (TMS (magneto NEAR resist\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:36
21	2	(257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and ((wir\$3 write) NEAR (line\$1 lead\$1)) and ((width length) WITH (greater longer) WITH (TMS (magneto NEAR resist\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:37
22	1704	(257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:14
23	292	((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:44
24	233	((((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit write) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:40
25	149	(((((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit write) NEAR (line\$1 lead\$1))) and (width length)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:40
26	237	((((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:15
27	150	(((((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))) and (width length)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:37
28	98	(((((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))) and (width length)) and (magnetic NEAR memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:36

29	12987	magnetic NEAR memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:14
30	1267	(magnetic NEAR memory) and (TMR MRAM (magneto NEAR resist\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:00
31	173	((magnetic NEAR memory) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 17:35
32	152	((magnetic NEAR memory) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:43
33	4	("5374578" "5389566" "5567636" "5659499").PN.	USPAT	2004/02/06 15:40
34	694	(TMR MRAM (magneto NEAR resist\$5)) WITH ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:32
35	347	((TMR MRAM (magneto NEAR resist\$5)) WITH ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))) and (magnetic NEAR memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:44
36	106	((TMR MRAM (magneto NEAR resist\$5)) WITH ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:36
37	701	(TMR MRAM (magneto NEAR resist\$5)) WITH (((wir\$3 bit metal write) (write NEAR word)) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:36
38	352	((TMR MRAM (magneto NEAR resist\$5)) WITH (((wir\$3 bit metal write) (write NEAR word)) NEAR (line\$1 lead\$1))) and (magnetic NEAR memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:24
39	110	((TMR MRAM (magneto NEAR resist\$5)) WITH (((wir\$3 bit metal write) (write NEAR word)) NEAR (line\$1 lead\$1))) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:36
40	71	((TMR MRAM (magneto NEAR resist\$5)) WITH (((wir\$3 bit metal write) (write NEAR word)) NEAR (line\$1 lead\$1))) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)) and (width length)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:37
41	0	10/615920	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 17:39

42	16248	(TMR MRAM (magneto NEAR resist\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:01
43	0	((TMR MRAM (magneto NEAR resist\$5))) and (step NEAR like NEAR difference)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:02
44	55	((TMR MRAM (magneto NEAR resist\$5))) and (step NEAR like)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:23
45	275	((TMR MRAM (magneto NEAR resist\$5))) and misalignment	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:23
46	49	((TMR MRAM (magneto NEAR resist\$5))) and misalignment) and (magnetic NEAR memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:24
47	8	("5732016" "5838608" "5949707" "5956267" "5982658" "5982660" "6005800" "6072717").PN.	USPAT	2004/02/06 18:44